

Low Noise RF Amplifier

- * Operating Frequency : 20-2000 MHz
- * Linear Power : +22 dBm
- * Saturated Power : +25 dBm
- * Noise Figure : 2.5 dB
- * Gain : 24 dB



Description: Designed for linear application in the 20-2000MHz range. This amplifier utilizes GaAs FET devices that provide high gain, wide dynamic range and excellent 3rd OIP.
Suggested applications: Multicarrier, Pulse, AM&FM modulation

ELECTRICAL SPECIFICATION @ VDD= +15VDC; Temp. = 25°C, 50Ω System

Parameter	Symbol	Min	Typ	Max	Unit
Operating Frequency	BW	20		2000	MHz
Gain	G	22	24		dB
Gain Flatness	ΔG		± 0.5	± 1.0	dB
Noise Figure (100-1000 MHz)	NF		2.5	5	dB
Power Output P1dB	P1dB	20	22		dBm
Output 3rd Order Intercept Point	OIP3	31	34		dBm
VSWR in/out	S11/S22		1.6 :1	2.0 :1	Ratio
Operating Voltage	Vdc		15	17	Volt
Operating Current	Id		250	300	mA

MECHANICAL SPECIFICATION

Parameter	Description	Limits	Units
Dimension	2.0 x 1.0 x 0.5		In
RF Connectors IN/OUT	SMA-F		
DC Connector	Filtered Solder Feed Thru		
Cooling	none		

PROTECTIONS

RF Input Power	15 dBm	
Reverse Polarity Protection	Option	
Load VSWR	Infinite up to 1W	
Stability	100% Tested	

ENVIROMENTAL CHARACTERISTICS

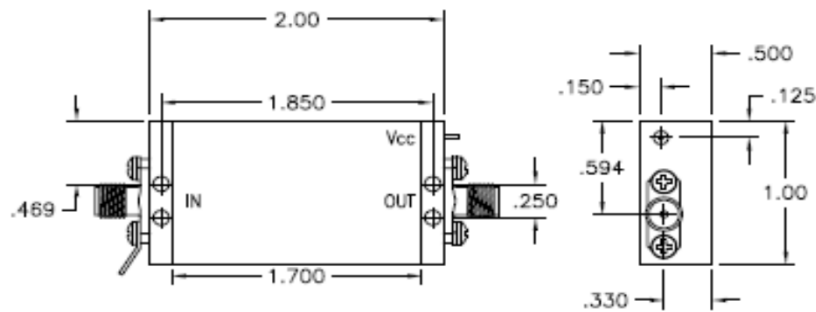
Parameter	Symbol	Min.	Typ.	Max.	Units
Operating Case Temperature	Tc	- 20°C		70°C	°C
Storage Temperature	Tstg	- 40C		120°C	°C

3009 Old State Rd, Telford, PA 18969

Web: www.amplifiersolutions.com
 Email: sales@amplifiersolutions.com

Tel: 215-799-2561
 Fax: 215-799-2563

Outline Drawing



3009 Old State Rd, Telford, PA 18969

Web: www.amplifiersolutions.com
Email: sales@amplifiersolutions.com

Tel: 215-799-2561
Fax: 215-799-2563